

- 14 -

BEST AVAILABLE COPY

What is claimed is:

1. A method of fabricating a wired board with bump electrodes, comprising the steps of:

5 forming a resist having an opening on a high-concentration impurity semiconductor base;

forming a conductive layer in said opening in said resist; and

10 forming a bump electrode on said wired board by aligning an electrode pad formed on said wired board with said conductive layer and then transferring said conductive layer to said electrode pad.

15 2. The fabrication method according to claim 1, wherein said high-concentration impurity semiconductor base has a pit formed at a position where said conductive layer should be formed.

3. The fabrication method according to claim 1, wherein the impurity of said high-concentration impurity semiconductor base is one selected from the group consisting of B, P, As, Sb and Pt.

20 4. The fabrication method according to claim 1, wherein said conductive layer is formed of one selected from the group consisting of Au, Cu, Ni, Pt, Pd, Ag, Sn and Pb, and an alloy thereof.

25 5. The fabrication method according to claim 1, wherein said conductive layer is formed of paste containing one selected from the group consisting of Au, Cu, Ni, Pt, Pd, Ag, Sn and Pb, and an alloy thereof.

6. The fabrication method according to claim 1,

- 15 -

wherein said conductive layer is formed by one method selected from the group consisting of electrolytic plating, electroless plating, sputtering, vapor deposition and printing.

5           7. The fabrication method according to claim 1, wherein at least the region on said high-concentration impurity semiconductor base where said conductive layer is formed are roughed.

10           8. The fabrication method according to claim 1, wherein at least the region on said high-concentration impurity semiconductor base where said conductive layer is formed are subjected to strike plating.

15           9. The fabrication method according to claim 2, wherein a size of said opening in said resist is smaller than a size of opening of said pit.

10           10. The fabrication method according to claim 2, wherein a size of said opening in said resist is larger than a size of opening of said pit.

20           11. The fabrication method according to claim 2, wherein the position of said opening in said resist is shifted from the position of opening of said pit.

25           12. The fabrication method according to claim 2, wherein said pit takes a shape selected from the group consisting of a pointed shape, a pentahedron shape, a pyramid shape and a hemispherical shape.

13. The fabrication method according to claim 2, wherein a depth of said pits is equal to or greater than 1/4 of a thickness of said resist.

BEST AVAILABLE COPY